

# 平成20年度賢材研究会会員活動報告書

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## 学術論文

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### 総説等

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### 特許

1. 2009.03.04、「断熱ガラスとその製造方法」奥原芳樹、松原秀彰、井須紀文、高田雅介、特願 2009-050707